





25V PNP HIGH PERFORMANCE TRANSISTOR IN SOT223

Features

- BV_{CEO} > -25V
- I_C = -3A High Continuous Current
- I_{CM} = -8A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < -300mV @ -1A
- Complementary NPN Type: FZT649
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 ³
- Weight: 0.112 grams (Approximate)

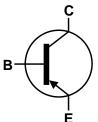
Applications

MOSFET and IGBT Gate Driving

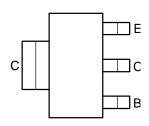
SOT223



Top View



Device Symbol



Top View Pin-Out

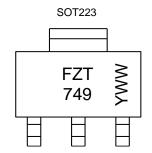
Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT749TA	AEC-Q101	FZT749	7	12	1,000
FZT749QTA	Automotive	FZT749	7	12	1,000
FZT749TC	AEC-Q101	FZT749	13	12	4,000
FZT749QTC	Automotive	FZT749	13	12	4,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



FZT 749 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-35	V
Collector-Emitter Voltage	V _{CEO}	-25	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-3	Α
Peak Pulse Current	Ісм	-8	А

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 6)		3.0		
Power Dissipation	(Note 7)	<u></u>	2.0	W	
Power Dissipation	(Note 8)	P_{D}	1.6		
	(Note 9)		1.2		
	(Note 6)		41.7		
Thermal Resistance, Junction to Ambient	(Note 7)	Б.	62.5		
Thermal Resistance, Junction to Ambient	(Note 8)	$R_{ hetaJA}$	78.1	°C/W	
	(Note 9)		104		
Thermal Resistance Junction to Lead (Note 10)		$R_{ hetaJL}$	12.9		
Operating and Storage Temperature Range	T_{J}, T_{STG}	-55 to +150	°C		

ESD Ratings (Note 9)

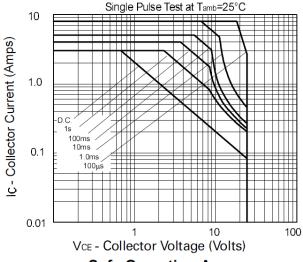
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

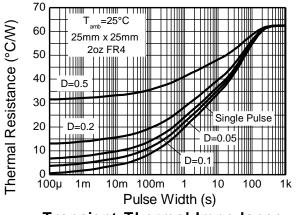
- 6. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 7. Same as Note 6, except the device is mounted on 25mm x 25mm 2oz copper.
- 8. Same as Note 6, except the device is mounted on 25mm x 25mm loz copper.
- 9. Same as Note 6, except the device is mounted on minimum recommended pad layout.
- 10. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 11. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



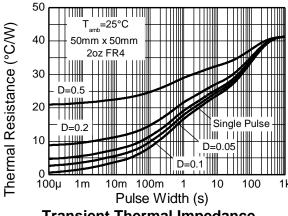
Thermal Characteristics and Derating Information



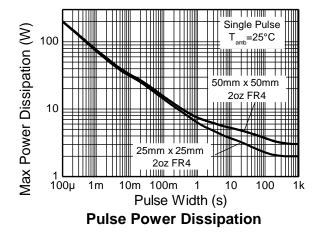
Safe Operating Area

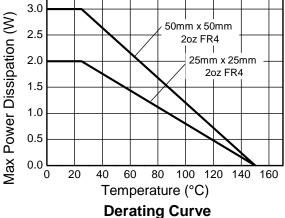


Transient Thermal Impedance



Transient Thermal Impedance









Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

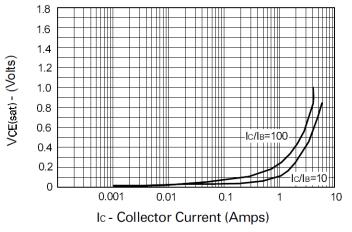
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-35	_	_	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 12)	BV _{CEO}	-25	_	_	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	_	_	V	I _E = -100μA
Callantar Cut Off Current		_	<1	-100	nA	V _{CB} = -30V
Collector Cut-Off Current	I _{CBO}	_	_	-10	μΑ	V _{CB} = -30V, T _{AMB} = +100°C
Emitter Cut-Off Current	I _{EBO}	_	<1	-100	nA	V _{EB} = -5.6V
Collector Emitter Seturation Voltage (Note 12)	V	_	-0.12	-0.3	V	I _C = -1A, I _B = -100mA
Collector-Emitter Saturation Voltage (Note 12)	$V_{CE(SAT)}$	_	-0.40	-0.6	\ \ \	I _C = -3A, I _B = -300mA
Base-Emitter Saturation Voltage (Note 12)	V _{CE(SAT)}	_	-0.9	-1.25	V	I _C = -1A, I _B = -100mA
Base-Emitter Turn-On Voltage (Note 12)	V _{BE(ON)}	_	-0.8	-1.0	V	I _C = -1A, V _{CE} = -2V
		70	200	_		I _C = -50mA, V _{CE} = -2V
DC Current Coin (Note 12)		100	200	300		I _C = -1A, V _{CE} = -2V
DC Current Gain (Note 12)	h _{FE}	75	570	_	-	I _C = -2A, V _{CE} = -2V
		15	50	_		I _C = -6A, V _{CE} = -2V
Current Gain-Bandwidth Product (Note 12)	f⊤	100	160	_	MHz	$V_{CE} = -5V, I_{C} = -100mA$ f = 100MHz
Turn-On Time	t _{on}	_	40	_	ns	V _{CC} = -10V, I _C = -500mA
Turn-Off Time	t _{off}	_	450	_	ns	$I_{B1} = I_{B2} = -50 \text{mA}$
Output Capacitance	C _{obo}	1	55	100	pF	V _{CB} = -10V, f = 1MHz

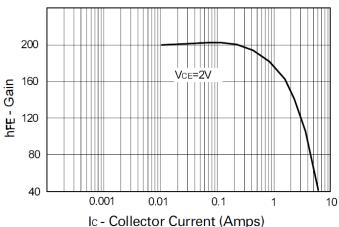
Note:

12. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.

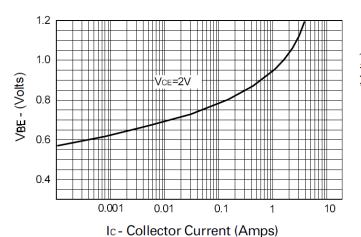


Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

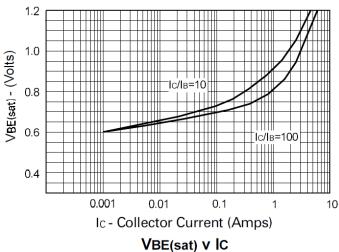




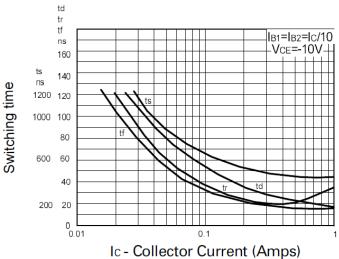
VCE(sat) v IC



hfe v IC



VBE(on) v IC



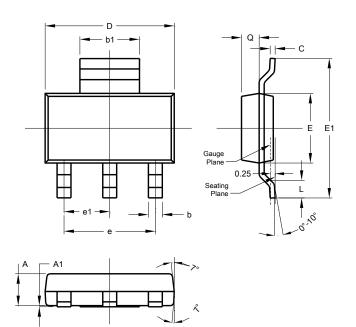
Switching Speeds





Package Outline Dimensions

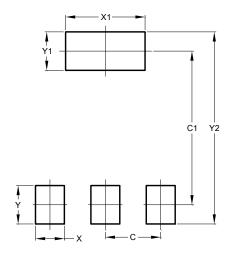
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
Х	1.20		
X1	3.30		
Y	1.60		
Y1	1.60		
Y2	8.00		





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